

## **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	60	V
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 5)	V <sub>GS</sub> = 10V	$T_A = +25$ °C $T_A = +85$ °C	I <sub>D</sub>	0.41 0.30	А
Pulsed Drain Current (Note 6)			I <sub>DM</sub>	2.64	Α

# Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Power Dissipation (Note 5)		$P_{D}$	0.47	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> =+25°C		$R_{\theta JA}$	258	°C/W
Operating and Storage Temperature Range		$T_{J}, T_{STG}$	-55 to +150	°C

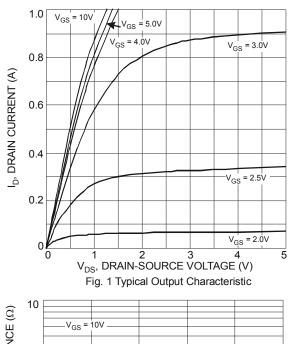
#### **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

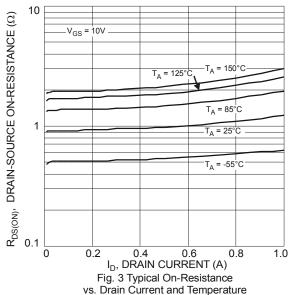
Characteristic	Symbol	Min	Тур	Max	Unit	Tes	t Condition
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	_	_	100	nA	V <sub>DS</sub> = 60V, V <sub>GS</sub> = 0V	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	10 1	μΑ	$V_{GS} = \pm 20V, V_{DS} = 0V$ $V_{GS} = \pm 5V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(th)</sub>	1.3	1.6	2.3	V	$V_{DS} = V_{GS}$ , I	<sub>D</sub> = 250µA
Static Drain-Source On-Resistance	J	_	_	1.40	Ω	V <sub>GS</sub> = 10V, I <sub>D</sub> = 40mA	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>			1.60		$V_{GS} = 4.5V$ ,	I <sub>D</sub> = 35mA
Forward Transfer Admittance	Y <sub>fs</sub>	100	_	_	mS	V <sub>DS</sub> = 5V, I <sub>D</sub> = 40mA	
Diode Forward Voltage	$V_{SD}$	_	0.7	1.1	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 300mA	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C <sub>iss</sub>	_	40	80	pF	V <sub>DS</sub> = 40V, V <sub>GS</sub> = 0V, f = 1.0MHz	
Output Capacitance	Coss	_	3.5	7	pF		
Reverse Transfer Capacitance	C <sub>rss</sub>	_	2.8	5.6	pF		
Gate Resistance	$R_g$	_	81.3	200	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz	
Total Gate Charge	Qg	_	0.73	1.5	nC	V <sub>GS</sub> = 4.5V	
Total Gate Charge	$Q_g$	_	1.39	2.8	nC	$V_{GS} = 10V$ $V_{DS} = 50V, I_{D} = 1A$	
Gate-Source Charge	$Q_{gs}$	_	0.2	0.4	nC		
Gate-Drain Charge	$Q_{gd}$	_	0.23	0.5	nC		
Turn-On Delay Time	t <sub>D(on)</sub>	_	3.89	10	ns	$V_{DS} = 50V, I_{D} = 1A$ $V_{GS} = 10V, R_{G} = 6\Omega$	
Turn-On Rise Time	t <sub>r</sub>		4.93	10	ns		
Turn-Off Delay Time	t <sub>D(off)</sub>		18.80	40	ns		
Turn-Off Fall Time	t <sub>f</sub>		11.96	25	ns		

Notes:

- 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
- 6. Device mounted on minimum recommended pad layout test board, 10µs pulse duty cycle = 1%.
- 7. Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to production testing.







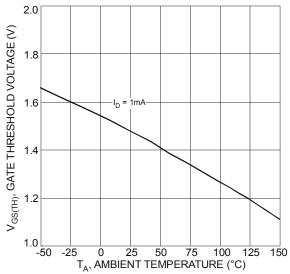


Fig. 5 Gate Threshold Variation vs. Ambient Temperature

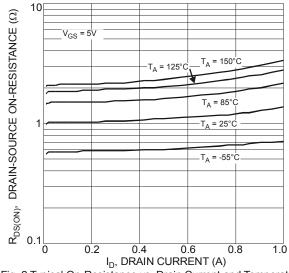


Fig. 2 Typical On-Resistance vs. Drain Current and Temperature

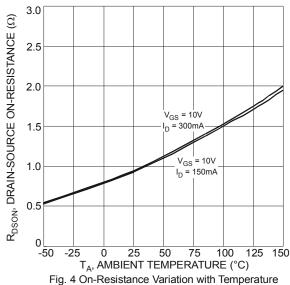


Fig. 4 On-Resistance Variation with Temperature

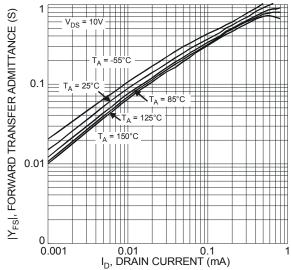
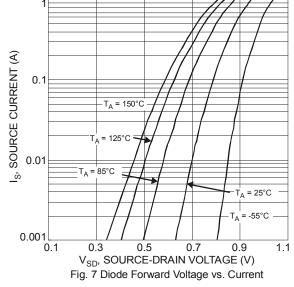
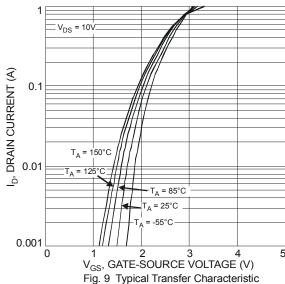
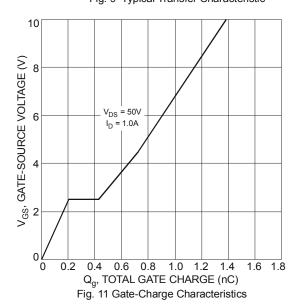


Fig. 6 Forward Transfer Admittance vs. Drain Current









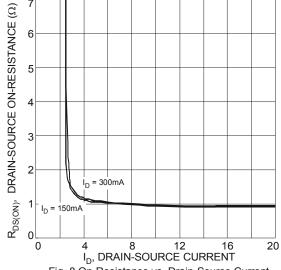
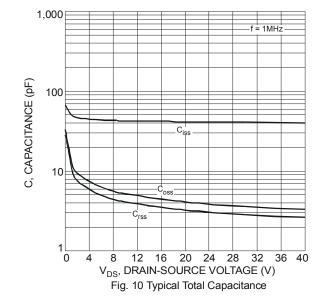
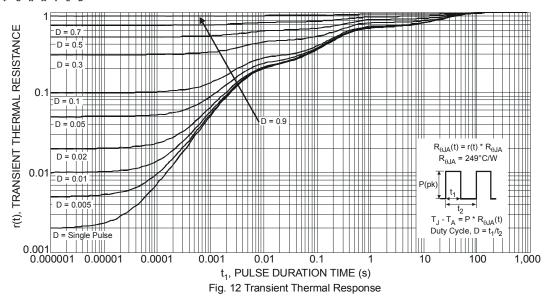


Fig. 8 On-Resistance vs. Drain-Source Current

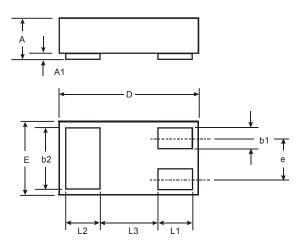






#### **Package Outline Dimensions**

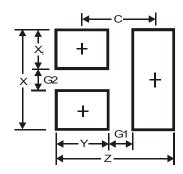
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



X1-DFN1006-3					
Dim	Min	Max	Тур		
Α	0.47	0.53	0.50		
A1	0	0.05	0.03		
b1	0.10	0.20	0.15		
b2	0.45	0.55	0.50		
D	0.95	1.075	1.00		
Е	0.55	0.675	0.60		
е	_	_	0.35		
L1	0.20	0.30	0.25		
L2	0.20	0.30	0.25		
L3			0.40		
All Dimensions in mm					

## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for latest version.



Dimensions	Value (in mm)		
Z	1.1		
G1	0.3		
G2	0.2		
Х	0.7		
X1	0.25		
Υ	0.4		
С	0.7		



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